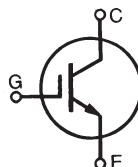


GenX3™ A3-Class IGBTs

IXGK120N120A3 IXGX120N120A3

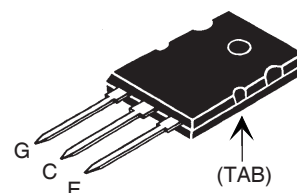
$$\begin{aligned} V_{CES} &= 1200V \\ I_{C110} &= 120A \\ V_{CE(sat)} &\leq 2.20V \end{aligned}$$

Ultra-Low V_{sat} PT IGBTs for
up to 3kHz Switching

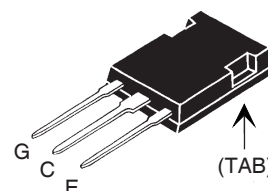


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1\text{M}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	240	A
I_{C110}	$T_C = 110^\circ\text{C}$	120	A
I_{LRMS}	Terminal Current Limit	75	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	600	A
SSOA (RBSOA)	$V_{GE} = 15\text{V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 240$ @ $0.8 \cdot V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	830	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ\text{C}$
M_d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXGX)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS 247™ (IXGX)



G = Gate E = Emitter
C = Collector TAB = Collector

Features

- Optimized for Low Conduction Losses
- Square RBSOA
- High Avalanche Capability
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{CE} = 0\text{V}$	1200		V
$V_{GE(th)}$	$I_C = 1\text{mA}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0\text{V}$ $T_J = 125^\circ\text{C}$			50 μA 3 mA
I_{GES}	$V_{CE} = 0\text{V}$, $V_{GE} = \pm 20\text{V}$			± 400 nA
$V_{CE(sat)}$	$I_C = 100\text{A}$, $V_{GE} = 15\text{V}$, Note 1	1.85	2.20	V

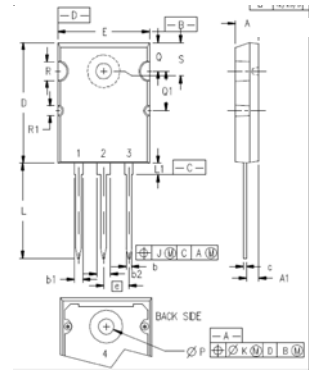
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 1	45	73	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		9900	pF
C_{oes}			655	pF
C_{res}			240	pF
$Q_{g(on)}$	$I_C = I_{C110}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		420	nC
Q_{ge}			70	nC
Q_{gc}			180	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$		40	ns
t_{ri}			67	ns
E_{on}			10	mJ
$t_{d(off)}$			490	ns
t_{fi}			325	ns
E_{off}	Note 2		33	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$		30	ns
t_{ri}			75	ns
E_{on}			15	mJ
$t_{d(off)}$			685	ns
t_{fi}			680	ns
E_{off}	Note 2		58	mJ
R_{thJC}				0.15 $^\circ\text{C/W}$
R_{thCK}			0.15	$^\circ\text{C/W}$

Note 1: Pulse Test, $t \leq 300\mu\text{s}$, Duty Cycle, $d \leq 2\%$.
 2. Switching Times may Increase for V_{CE} (Clamp) $> 0.8 V_{CES}$,
 Higher T_J or Increased R_G .

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

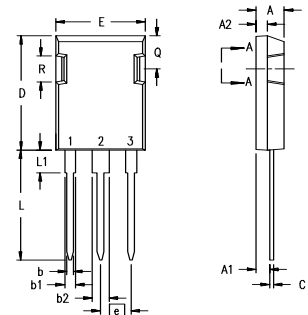
TO-264 (IXGK) Outline



1 - GATE
 2, 4 - DRAIN (COLLECTOR)
 3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b1	.037	.055	0.94	1.40
b2	.087	.102	2.21	2.59
c	.110	.126	2.79	3.20
D	.017	.029	0.43	0.74
E	1.007	1.047	25.58	26.59
e	.760	.799	19.30	20.29
J	.215BSC		5.46	BSC
K	.000	.010	0.00	0.25
L	.000	.010	0.00	0.25
L1	.779	.842	19.79	21.39
Q	.087	.102	2.21	2.59
Q1	.122	.138	3.10	3.51
R	.240	.256	6.10	6.50
R1	.330	.346	8.38	8.79
S	.155	.187	3.94	4.75
	.085	.093	2.16	2.36
	.243	.253	6.17	6.43

PLUS 247™ (IXGX) Outline



Terminals: 1 - Gate
 2 - Drain (Collector)
 3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
 by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics
@ 25°C

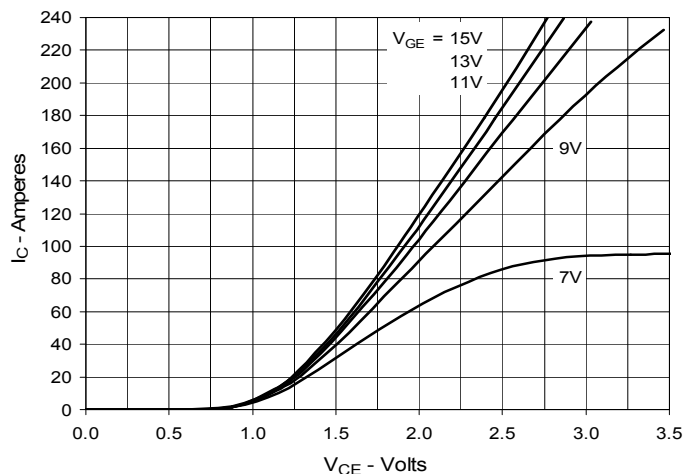


Fig. 2. Extended Output Characteristics
@ 25°C

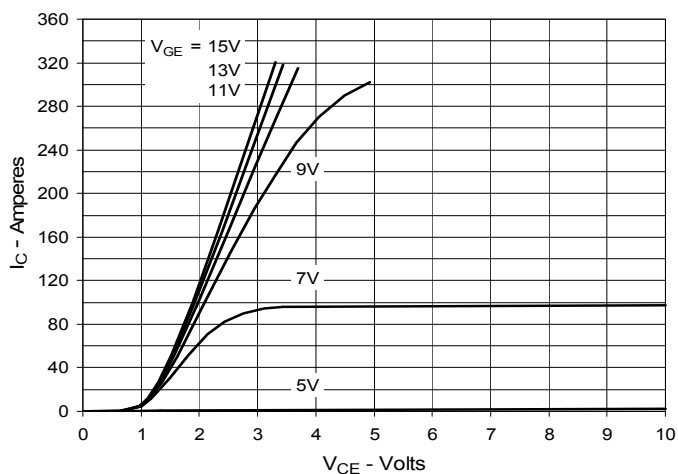


Fig. 3. Output Characteristics
@ 125°C

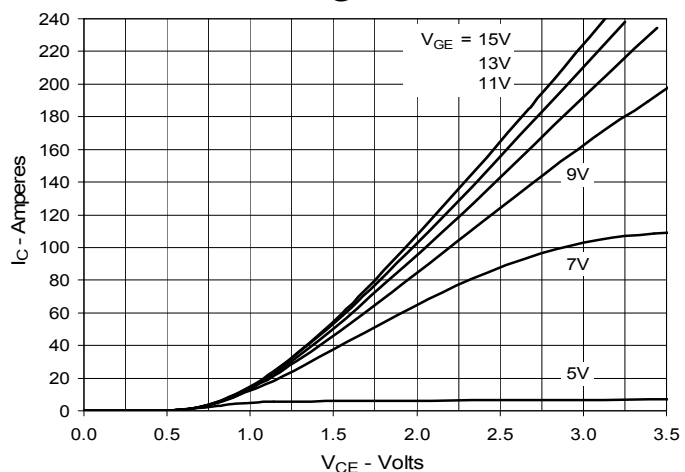


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

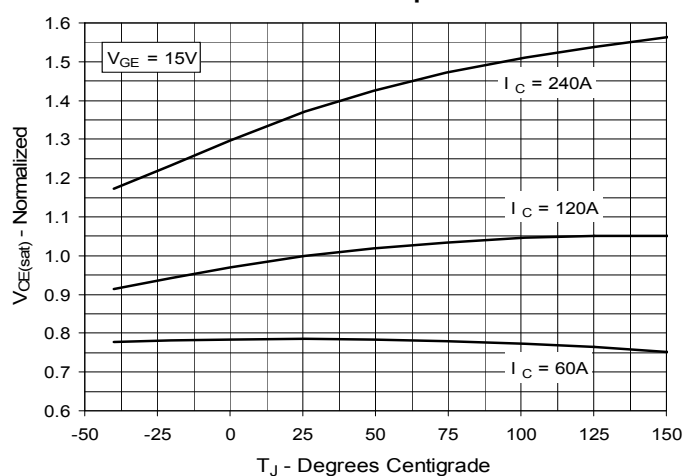


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

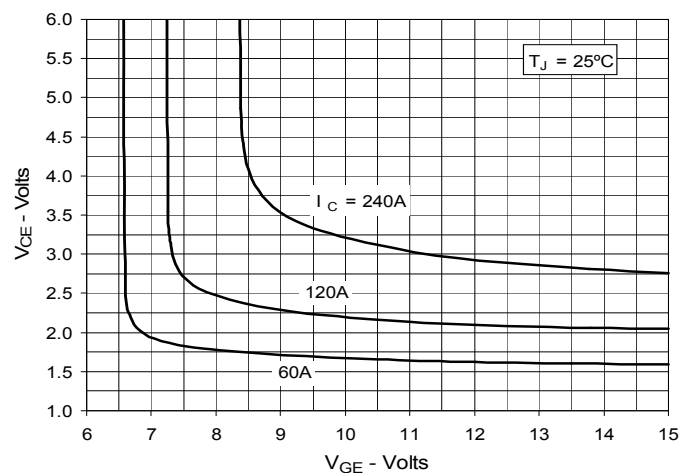


Fig. 6. Input Admittance

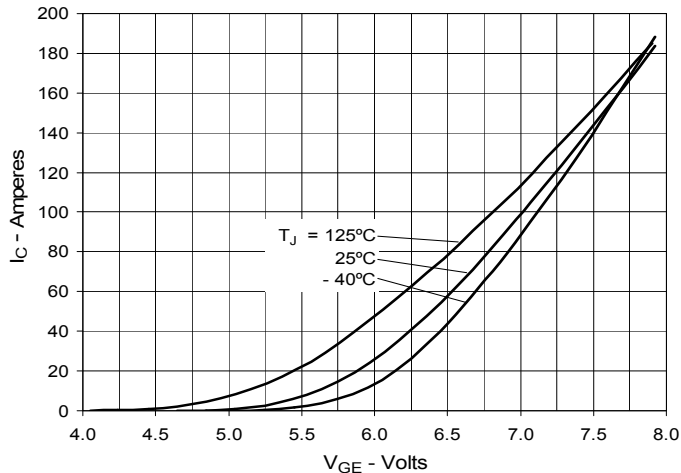


Fig. 7. Transconductance

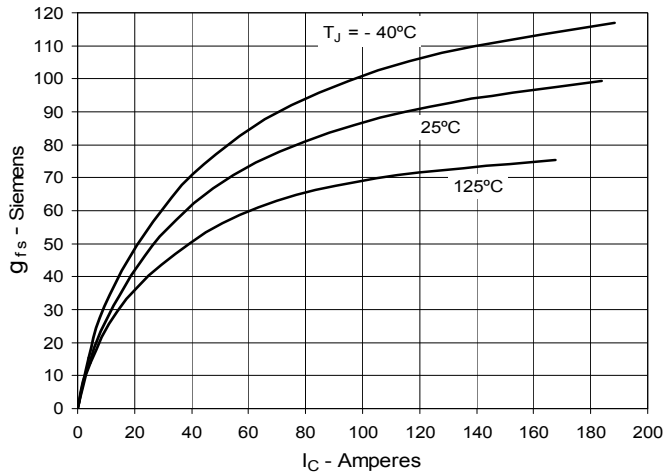


Fig. 8. Gate Charge

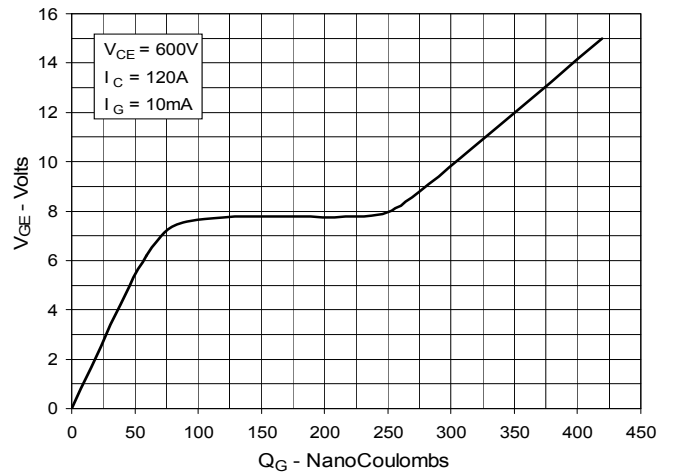


Fig. 9. Capacitance

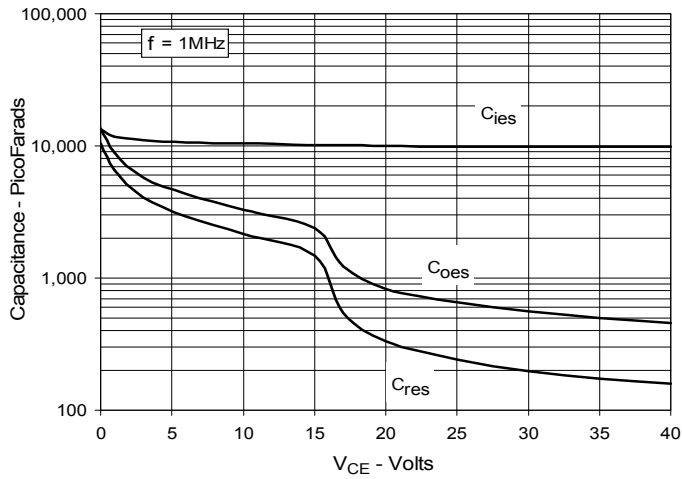


Fig. 10. Reverse-Bias Safe Operating Area

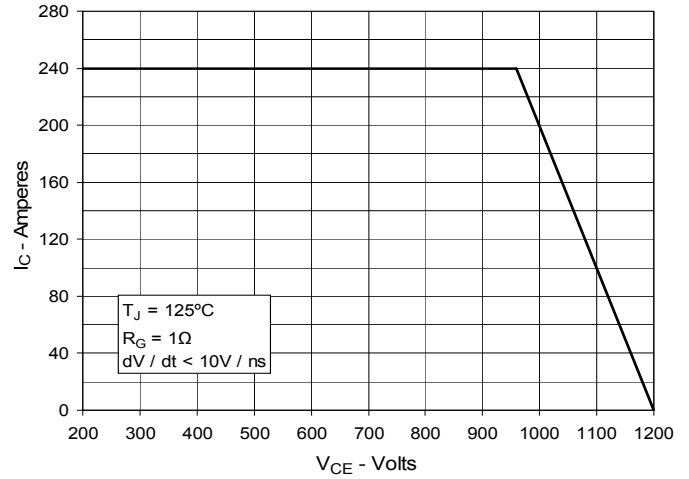
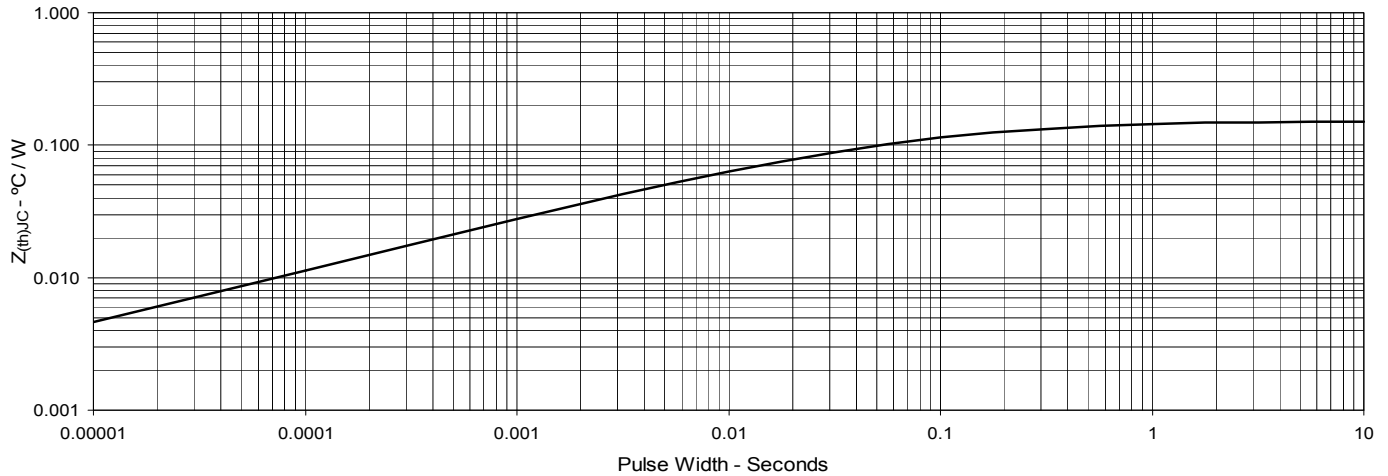
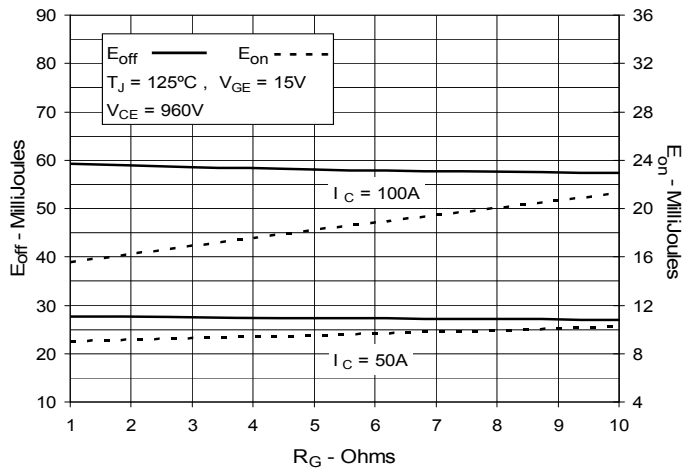


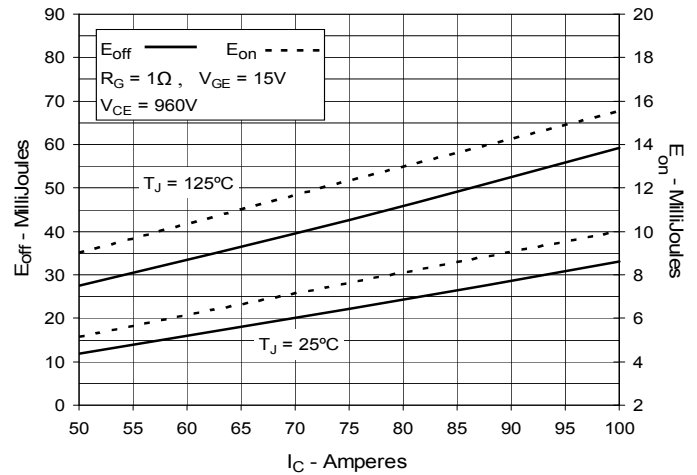
Fig. 11. Maximum Transient Thermal Impedance



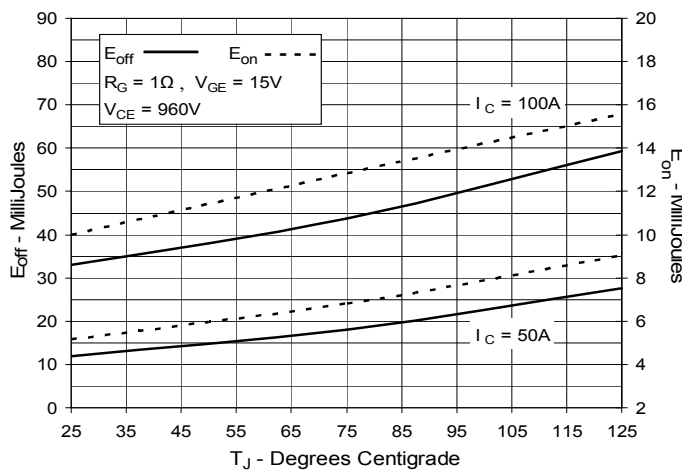
**Fig. 12. Inductive Switching
Energy Loss vs. Gate Resistance**



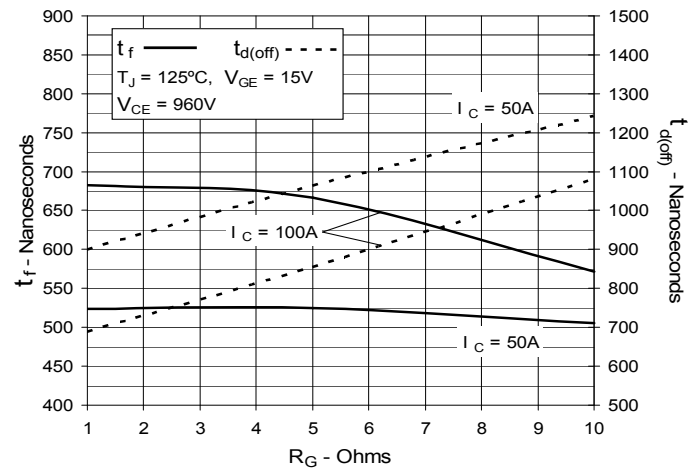
**Fig. 13. Inductive Switching
Energy Loss vs. Collector Current**



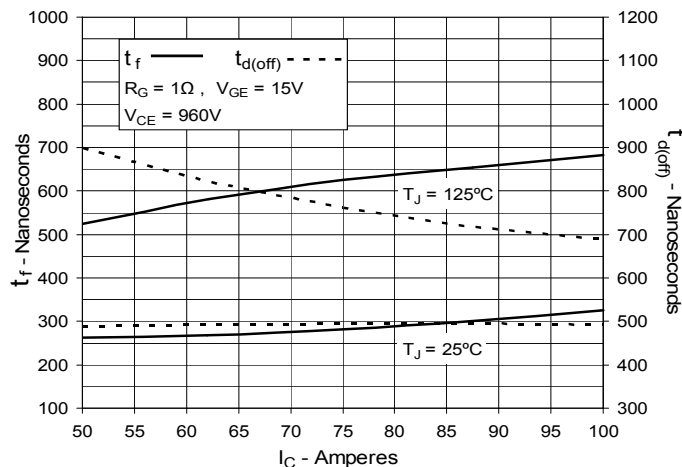
**Fig. 14. Inductive Switching
Energy Loss vs. Junction Temperature**



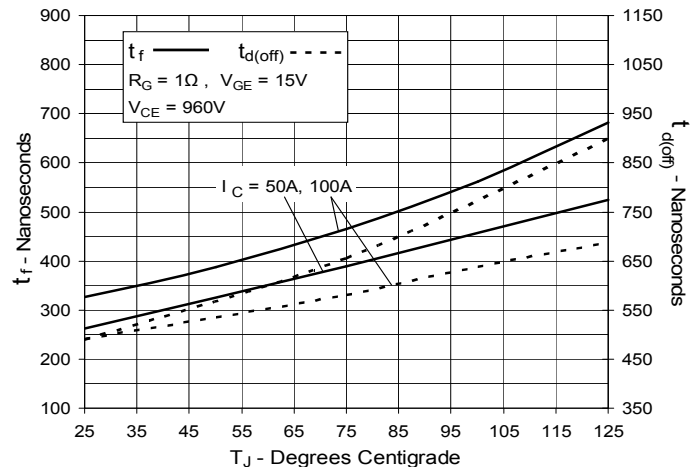
**Fig. 15. Inductive Turn-off
Switching Times vs. Gate Resistance**



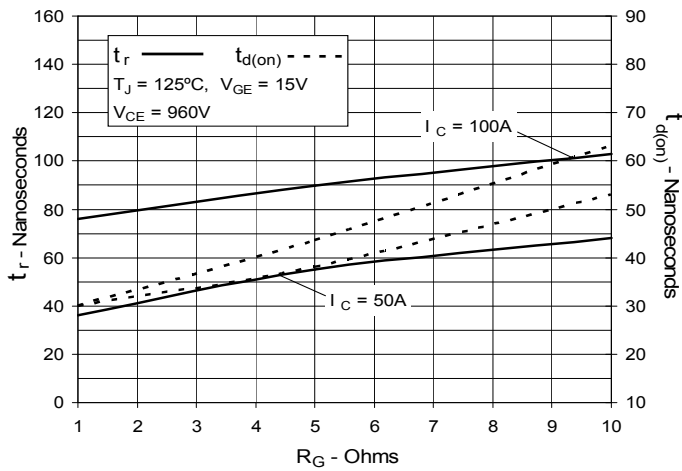
**Fig. 16. Inductive Turn-off
Switching Times vs. Collector Current**



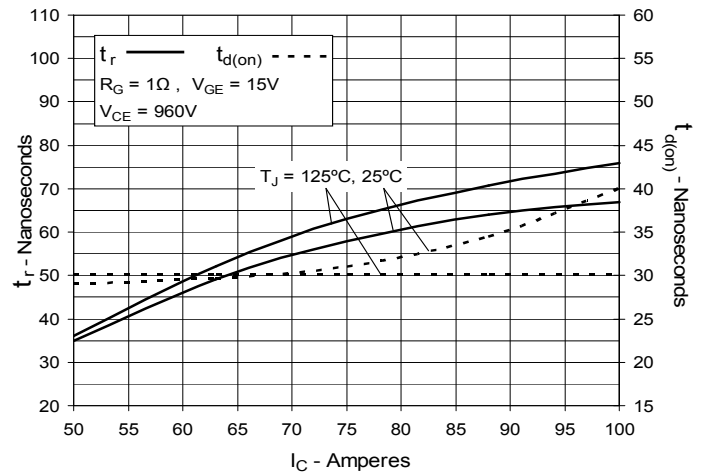
**Fig. 17. Inductive Turn-off
Switching Times vs. Junction Temperature**



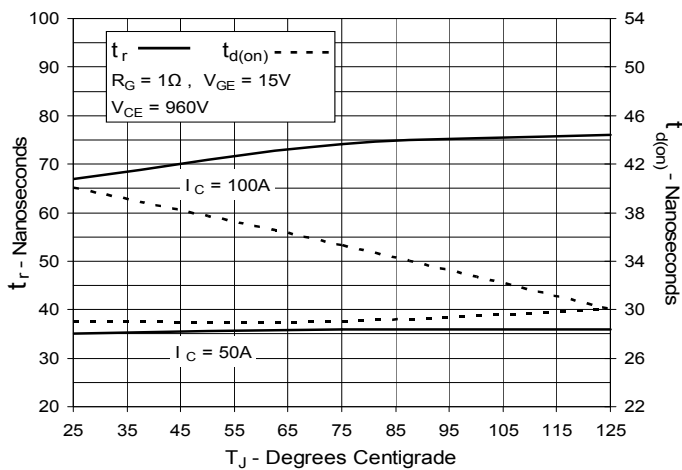
**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**





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